

描述 / Descriptions

PDFN5*6 封装 N 沟道场效应管。

N-Channel MOSFET in a PDFN5*6 Plastic Package .

特征 / Features

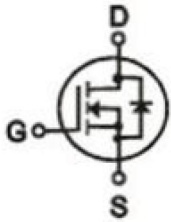
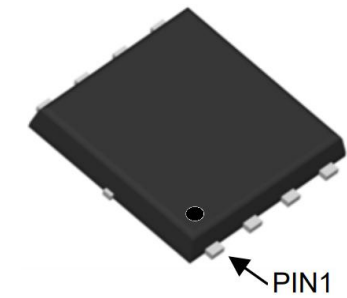
低电阻可最大地降低导电损耗；低栅极电荷，可实现快速切换；低热阻。

Low $R_{DS(ON)}$ to minimize conductive loss; low Gate Charge for fast switching; Low Thermal resistance.

用途 / Applications

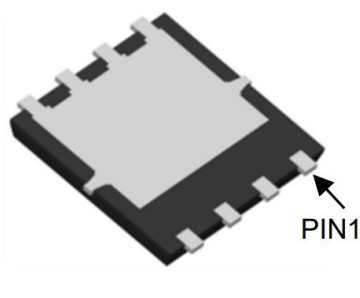
电池管理

Battery Management

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1、2、3: S

PIN4: G



PIN5、6、7、8: D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.


极限参数 / Absolute Maximum Ratings($T_a=25^{\circ}\text{C}$)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	40	V
Drain Current - Continuous	I_D	100	A
Drain Current – Pulsed	I_{DM}	230	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	$P_D(T_c=25^{\circ}\text{C})$	114	W
Single Pulse Avalanche Energy($L=0.5\text{mH}$)	E_{AS}	428.75	mJ
Avalanche Current($L=0.5\text{mH}$)	I_{AS}	35	A
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$
Thermal resistance, junction - case	$R_{\theta JC}$	1.5	$^{\circ}\text{C/W}$
Thermal resistance, junction - ambient	$R_{\theta JA}$	55	$^{\circ}\text{C/W}$

电性能参数 / Electrical Characteristics($T_a=25^{\circ}\text{C}$)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	40	50		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40\text{V}, V_{GS}=0\text{V}$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.45	2	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		1.2	1.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		1.6	2.0	
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		5800		pF
Output Capacitance	C_{oss}			1860		
Reverse Transfer Capacitance	C_{rss}			135		
Gate resistance	R_g	$V_{GS}=0\text{V}, V_{DS}=0\text{V}$ $f=1\text{MHz}$		1.25		Ω
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}, V_{DS}=20\text{V},$ $I_D=20\text{A}$		70		nC
Total Gate Charge	$Q_g(4.5\text{V})$			30		
Gate Source Charge	Q_{gs}			14.5		
Gate Drain Charge	Q_{gd}			10.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}, V_{DS}=20\text{V},$ $R_L=1\Omega, R_{GEN}=3\Omega$		15		ns
Turn-On Rise Time	t_r			5.8		
Turn-Off Delay Time	$t_{d(off)}$			62		
Turn-Off Fall Time	t_f			10		

电参数曲线图 / Electrical Characteristic Curve

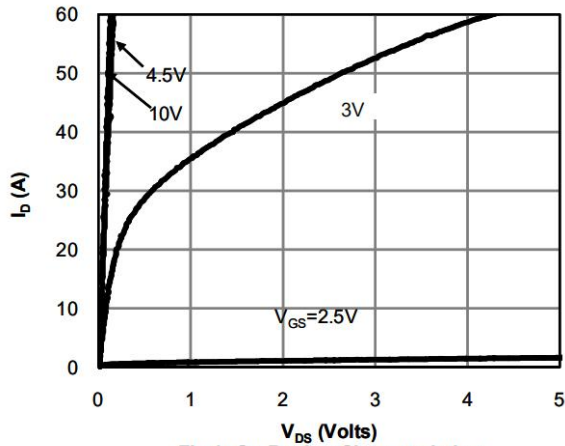


Fig 1: On-Region Characteristics

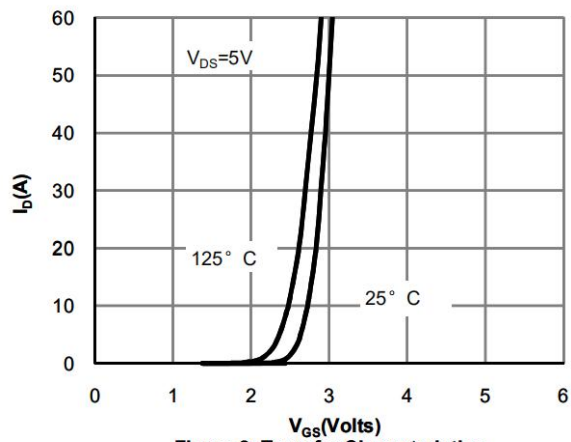


Figure 2: Transfer Characteristics

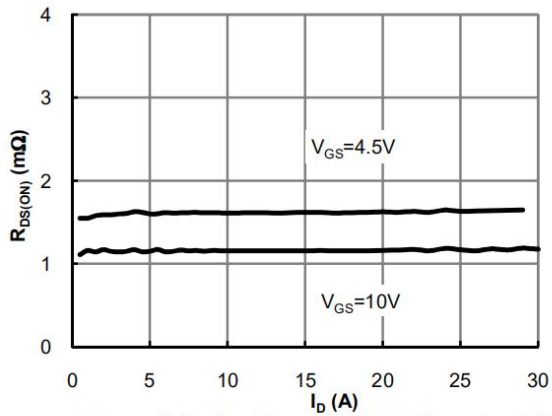


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

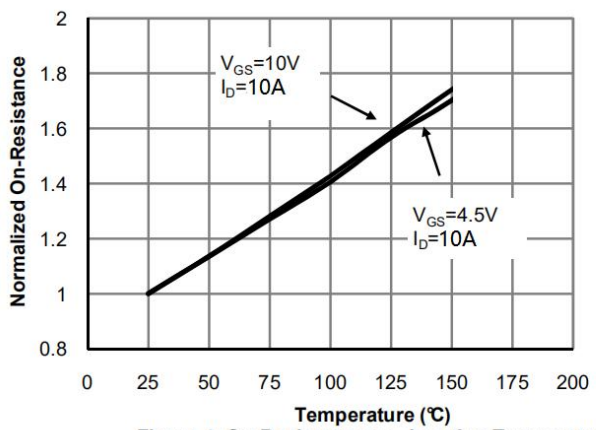


Figure 4: On-Resistance vs. Junction Temperature

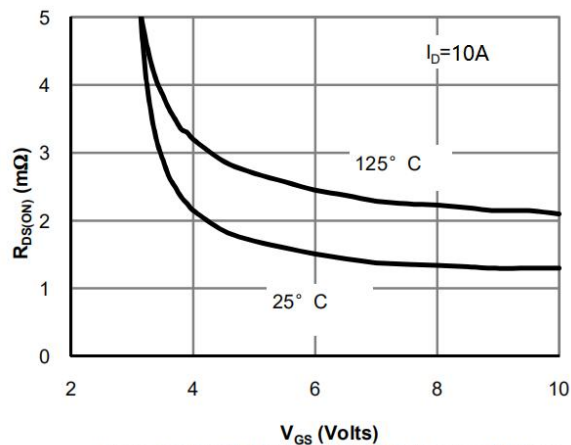


Figure 5: On-Resistance vs. Gate-Source Voltage

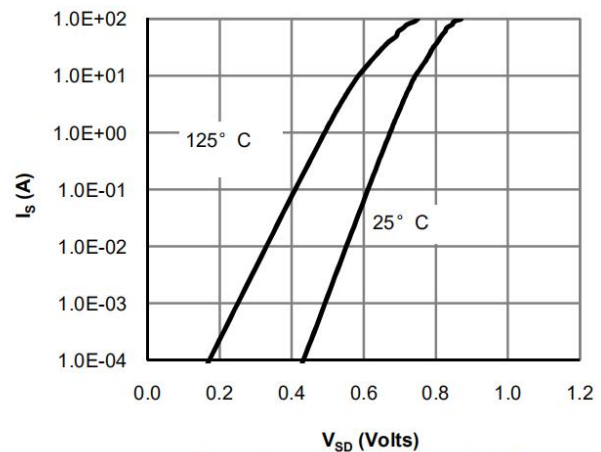
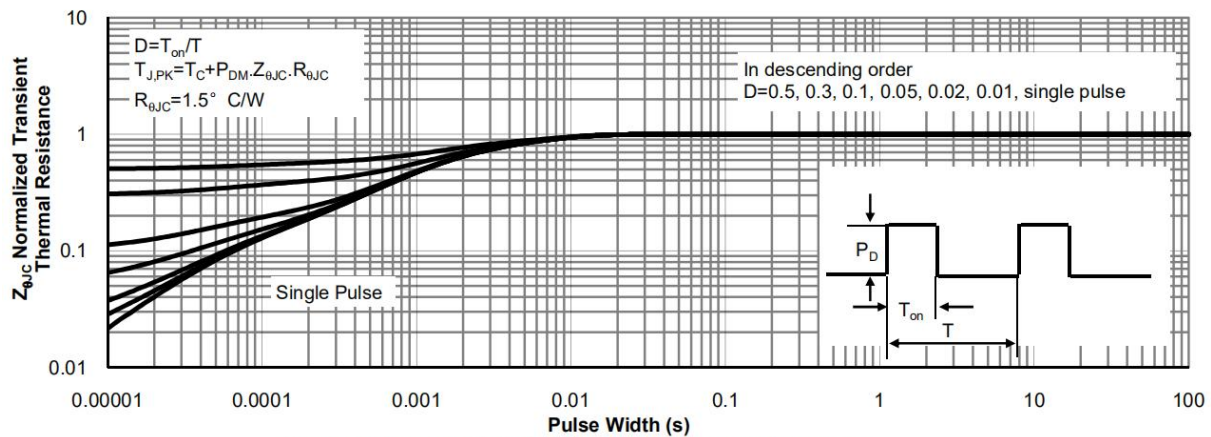
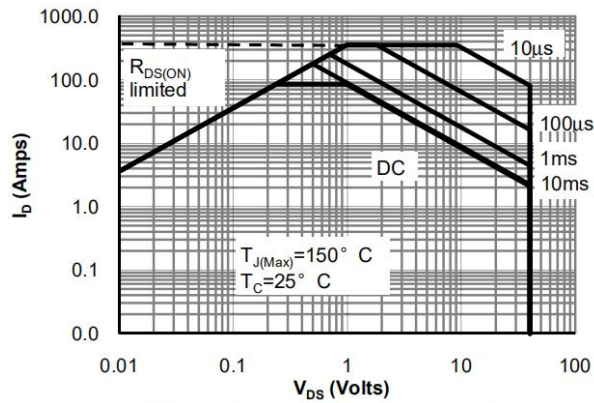
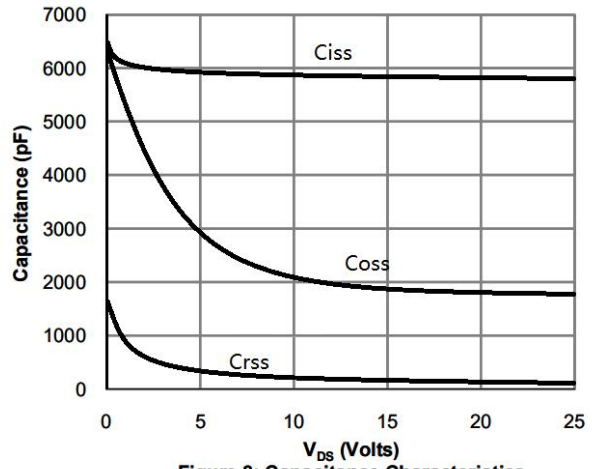
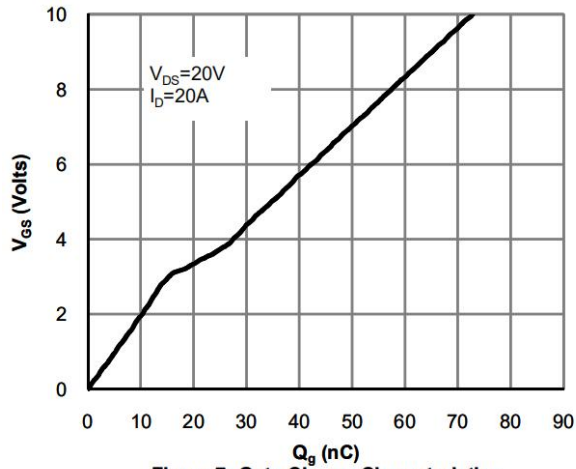


Figure 6: Body-Diode Characteristics

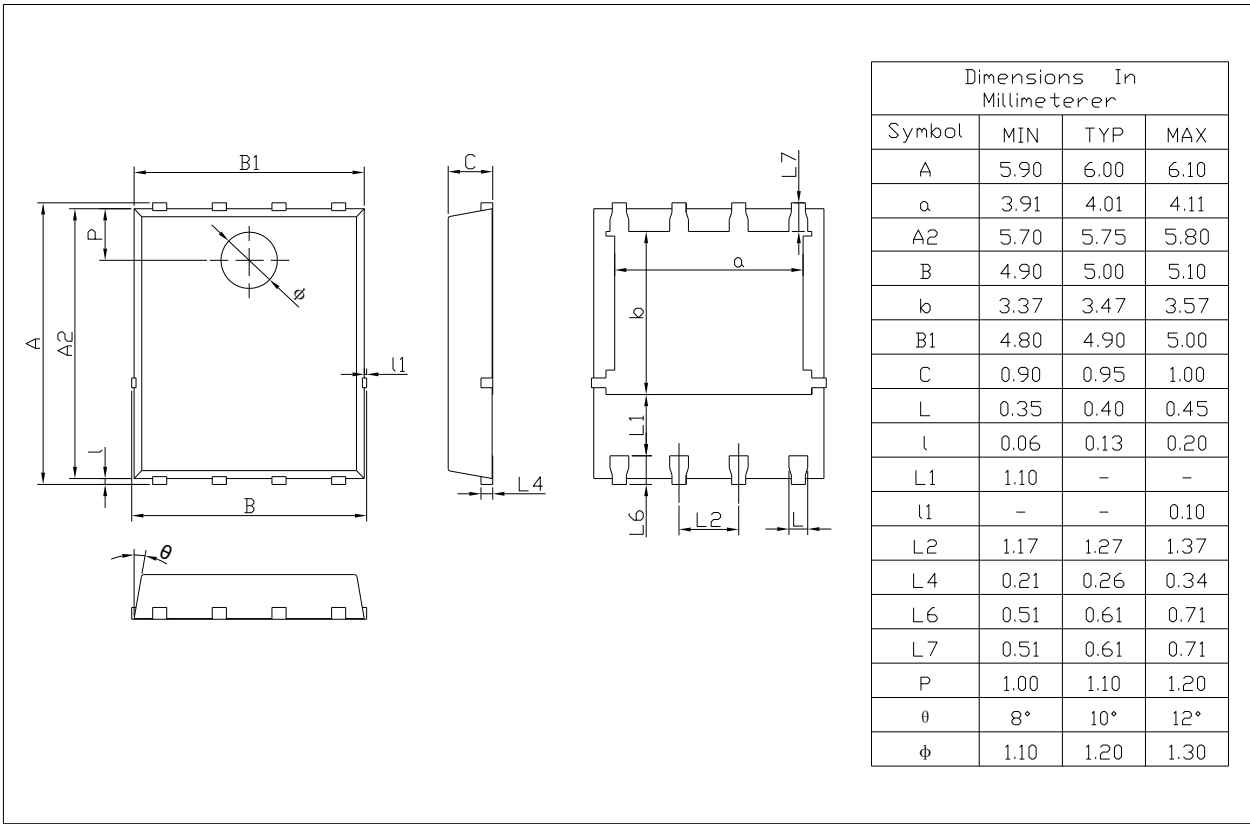
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

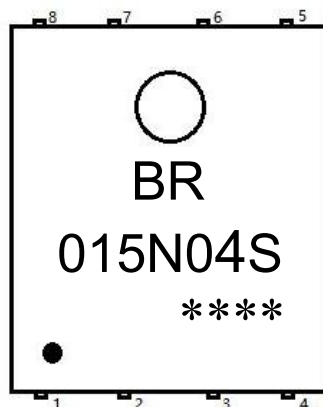
PDFN5 X6

Unit:mm



Rev.00 201812

印章说明 / Marking Instructions



说明：

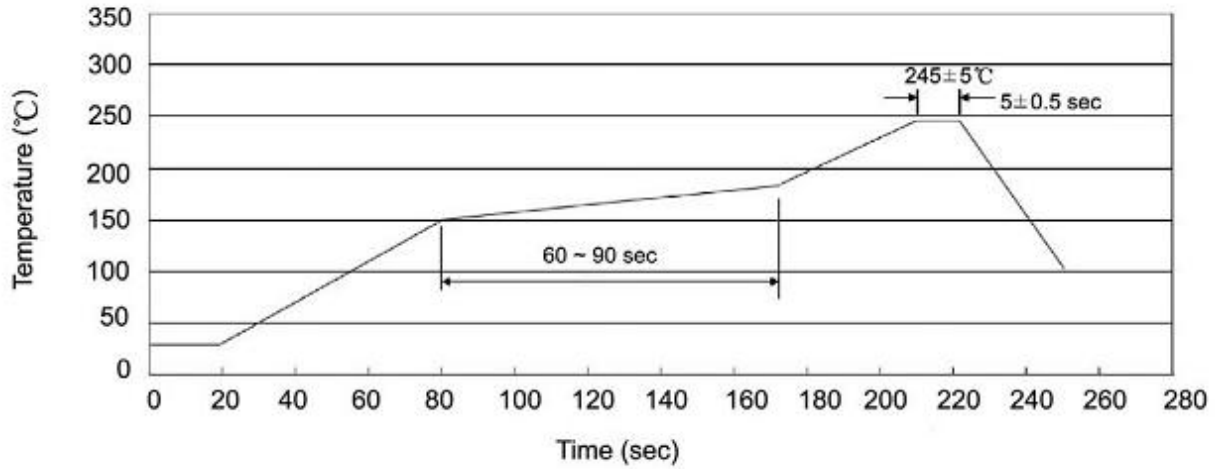
BR： 为公司代码

015N04S： 为为产品型号

Note：

BR： Company Code

015N04S： Product Type.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN5*6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

使用说明 / Notices